

GOOD-ARK



SEMICONDUCTOR

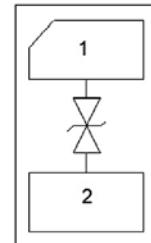
**GSEZ6B2000****ESD Protection Diode**

## Features

- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Operating voltage: 6.3V
- Low clamping voltage
- 2-Pin leadless package
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test Air discharge:  $\pm 30\text{kV}$
  - Contact discharge:  $\pm 30\text{kV}$
  - IEC 61000-4-5 (Lightning) 90A (8/20 $\mu\text{s}$ )



DFN1006



Schematic Diagram

## Applications

- Cellular handsets and accessories
- Personal digital assistants
- Notebooks and handhelds
- Portable instrumentation
- Digital cameras
- Peripherals

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 $\mu\text{s}$ )	$P_{pk}$	1485	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	$I_{PP}$	90	A
ESD Per IEC 61000-4-2 (Air)	$V_{ESD}$	$\pm 30$	kV
ESD Per IEC 61000-4-2 (Contact)		$\pm 30$	
Operating Temperature Range	$T_J$	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	$V_{RWM}$	-	-	-	6.3	V
Breakdown Voltage	$V_{BR}$	$I_T=1\text{mA}$	6.5	-	9.5	V
Reverse Leakage Current	$I_R$	$V_{RWM}=6.3\text{V}$	-	-	0.5	$\mu\text{A}$
Clamping Voltage <sup>1</sup>	$V_C$	$I_{PP}=90\text{A}$ (8 x 20 $\mu\text{s}$ pulse)	-	-	16.5	V
		$I_{PP}=4\text{A}$ , $t_p=0.2/100\text{ns}$ (TLP)	-	7.1	-	V
		$I_{PP}=16\text{A}$ , $t_p=0.2/100\text{ns}$ (TLP)	-	7.8	-	V
Dynamic Resistance <sup>2</sup>	$R_{DYN}$	$t_p=0.2/100\text{ns}$ (TLP)	-	0.06	-	$\Omega$
Junction Capacitance	$C_J$	$V_R=0\text{V}$ , $f=1\text{MHz}$	-	200	-	pF

Notes:

1. Transmission Line Pulse test (TLP) settings:  $t_p=100\text{ns}$ ,  $t_i=0.2\text{ns}$ .
2. Dynamic resistance calculated from  $I_{TLP}=4\text{A}$  to  $I_{TLP}=16\text{A}$ .

**Typical Performance Characteristics** ( $T_A=25^\circ\text{C}$  unless otherwise Specified)

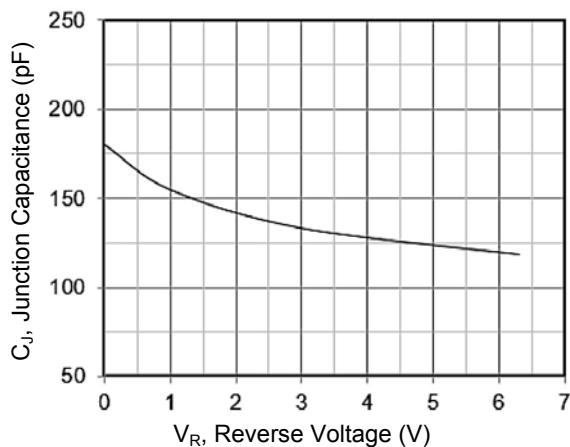


Figure 1. Junction Capacitance vs. Reverse Voltage

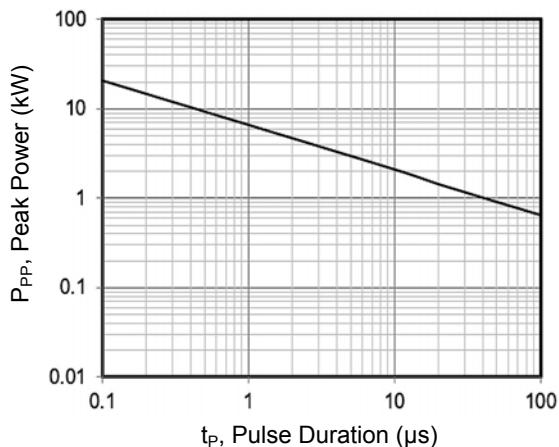


Figure 2. Peak Pulse Power vs. Pulse Time

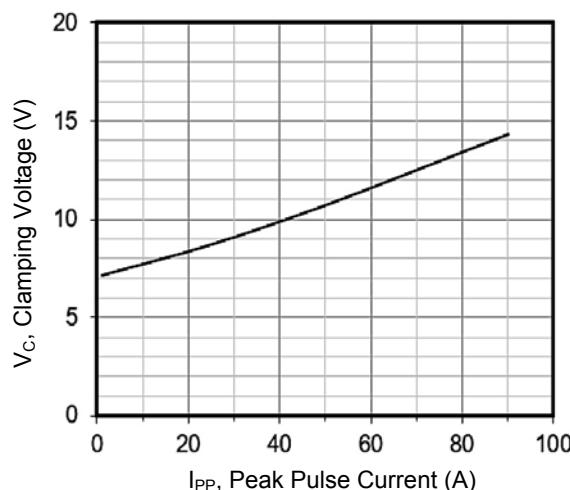


Figure 3. Clamping Voltage vs. Peak Pulse Current

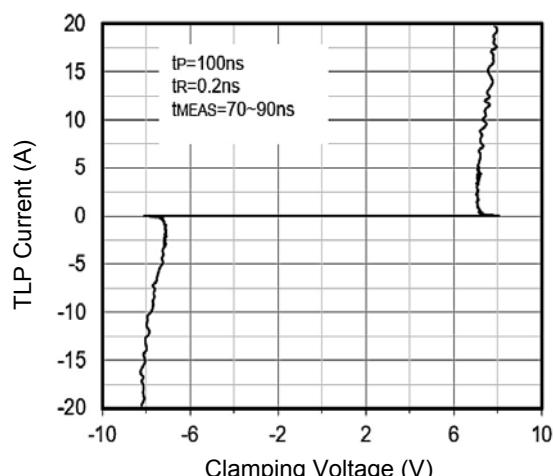


Figure 4. TLP Measurement

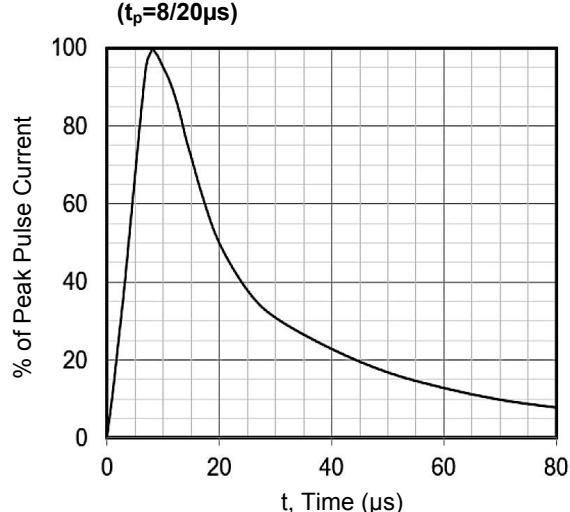


Figure 5. 8 x 20μs Pulse Waveform

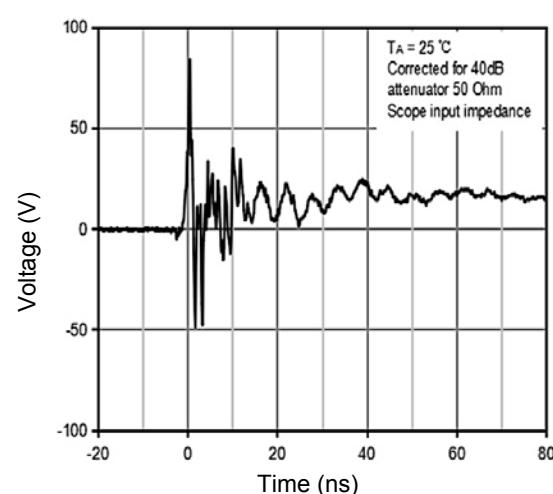
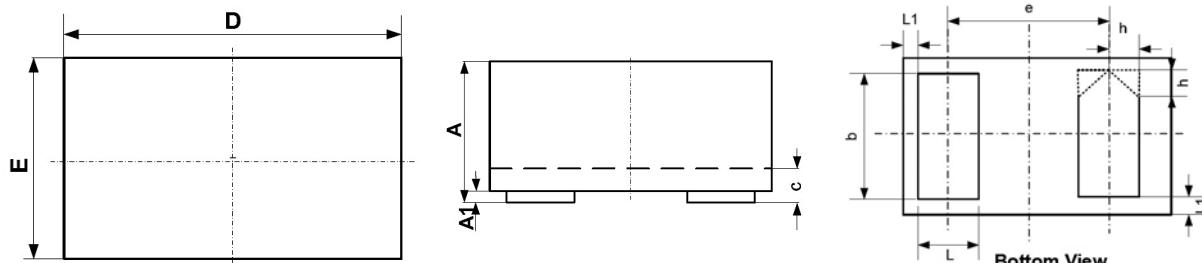


Figure 6. ESD Clamping Voltage

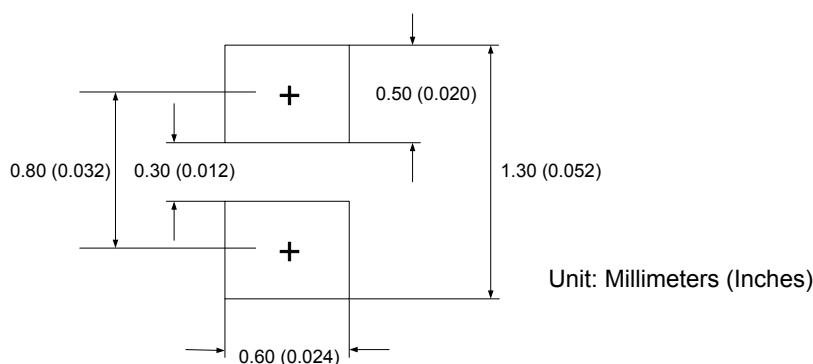
8 kV Contact Per IEC61000-4-2

### Package Outline Dimensions (DFN1006)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.40	0.55	0.016	0.022
A1	0.00	0.05	0.000	0.002
b	0.45	0.55	0.018	0.022
c	0.12	0.18	0.005	0.007
D	0.95	1.05	0.037	0.041
e	0.65 BSC		0.026 BSC	
E	0.55	0.65	0.022	0.026
L	0.20	0.30	0.008	0.012
L1	0.05 REF		0.002 REF	
h	0.07	0.17	0.003	0.007

### Recommended Pad Layout



### Order Information

Device	Package	Marking	Carrier	Quantity
GSEZ6B2000	DFN1006	C8	Tape & Reel	10,000 Pcs / Reel

For more information, please contact us at: [inquiry@goodarksemi.com](mailto:inquiry@goodarksemi.com)